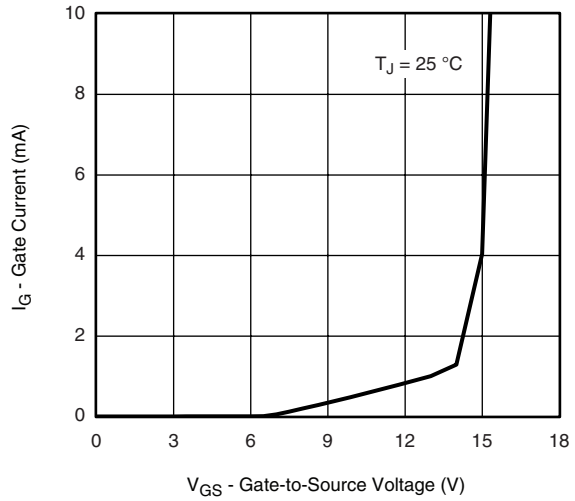
SPECIFICATIONS T_J = 25 °C, unless otherwise noted						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = - 250 µA	- 20			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	I_D = - 250 µA		- 15		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			2.6		
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = - 250 µA	- 0.4		- 1	V
Gate-Source Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 4.5 V			± 4	µA
		V_{DS} = 0 V, V_{GS} = ± 12 V			± 8	mA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = - 20 V, V_{GS} = 0 V			- 1	µA
		V_{DS} = - 20 V, V_{GS} = 0 V, T_J = 55 °C			- 10	
On-State Drain Current[a]	$I_{D(on)}$	$V_{DS} \leq$ - 5 V, V_{GS} = - 4.5 V	- 10			A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = - 4.5 V, I_D = - 4.2 A		0.050	0.06	Ω
		V_{GS} = - 3.6 V, I_D = - 4.0 A		0.053	0.065	
		V_{GS} = - 2.5 V, I_D = - 3.6 A		0.065	0.080	
		V_{GS} = - 1.8 V, I_D = - 2 A		0.091	0.120	
Forward Transconductance[a]	g_{fs}	V_{DS} = - 10 V, I_D = - 4.2 A		15		S
Dynamic[b]						
Gate Resistance	R_g	f = 1 MHz	1.2	6	12	kΩ
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = - 10 V, R_L = 2.2 Ω $I_D \cong$ - 4.5 A, V_{GEN} = - 4.5 V, R_g = 1 Ω		1.2	2.4	µs
Rise Time	t_r			5	10	
Turn-Off Delay Time	$t_{d(off)}$			14	28	
Fall Time	t_f			10	20	
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = - 10 V, R_L = 2.2 Ω $I_D \cong$ - 4.5 A, V_{GEN} = - 10 V, R_g = 1 Ω		0.5	1	
Rise Time	t_r			1.4	2.8	
Turn-Off Delay Time	$t_{d(off)}$			20	40	
Fall Time	t_f			10	20	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	T_C = 25 °C			- 4.5	A
Pulse Diode Forward Current	I_{SM}				- 15	
Body Diode Voltage	V_{SD}	I_S = - 4.5 A, V_{GS} = 0 V		- 0.9	- 1.2	V
Body Diode Reverse Recovery Time	t_{rr}	I_F = - 4.5 A, dI/dt = 100 A/µs, T_J = 25 °C		20	40	ns
Body Diode Reverse Recovery Charge	Q_{rr}			11	20	nC
Reverse Recovery Fall Time	t_a			12		ns
Reverse Recovery Rise Time	t_b			8		

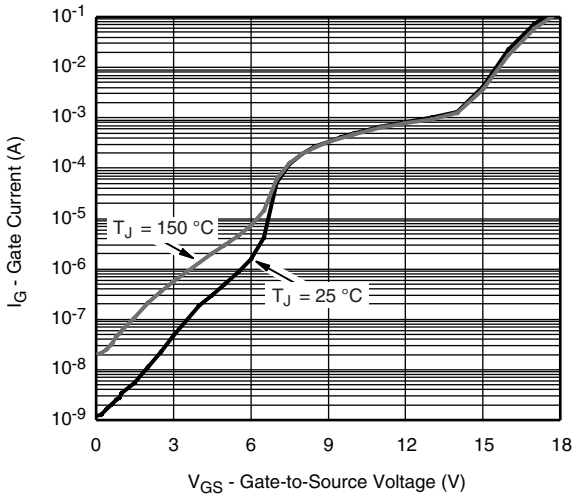
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

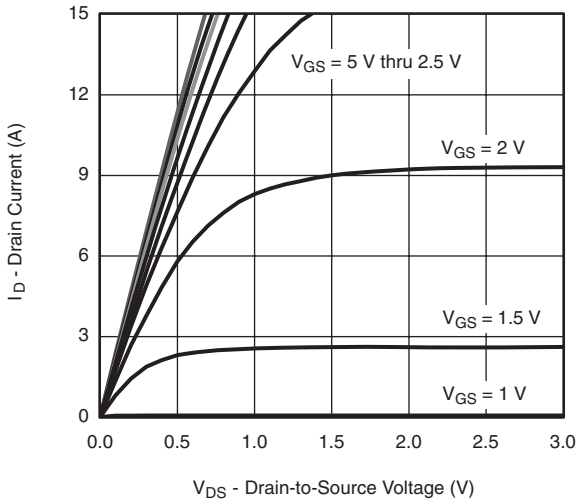
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



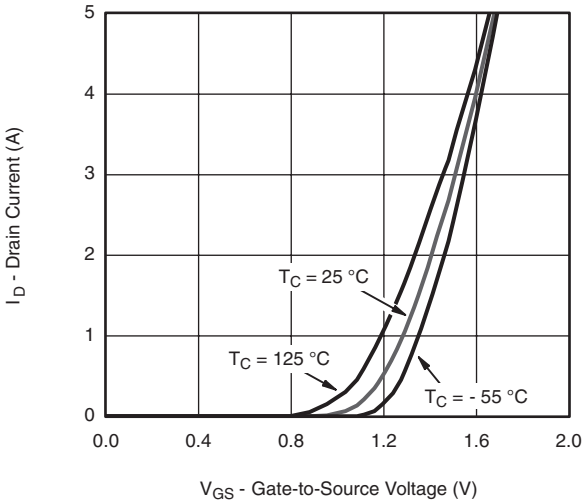
Gate Current vs. Gate-to-Source Voltage



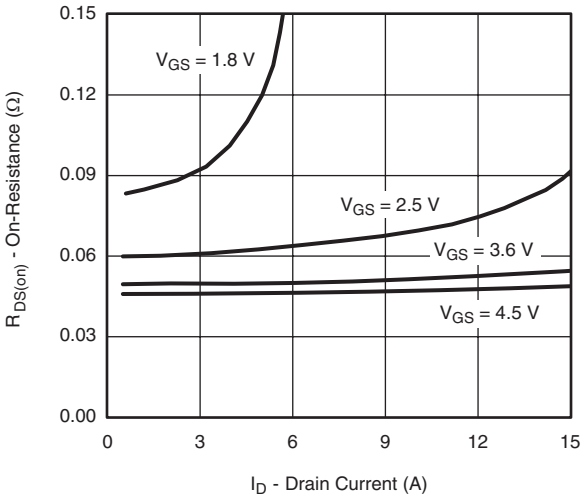
Gate Current vs. Gate-to-Source Voltage



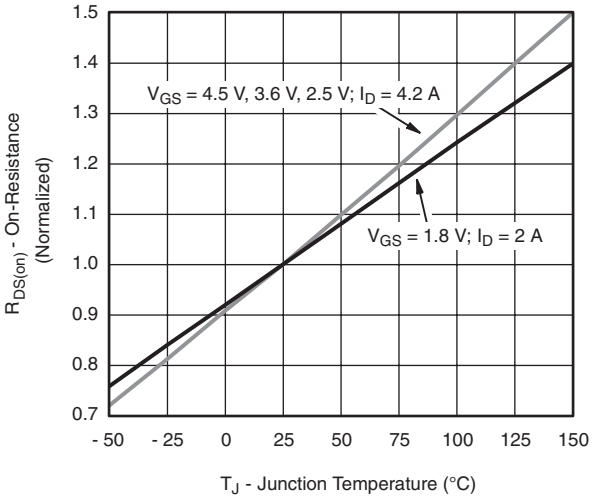
Output Characteristics



Transfer Characteristics

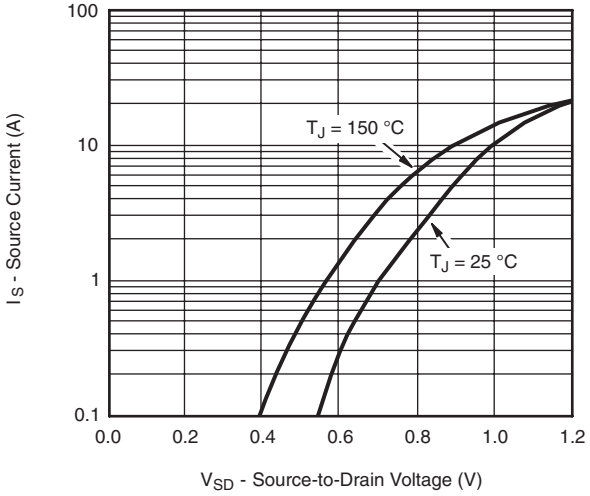


On-Resistance vs. Drain Current

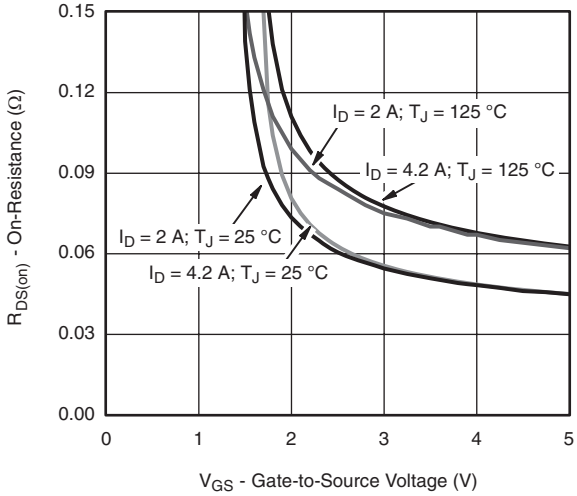


On-Resistance vs. Junction Temperature

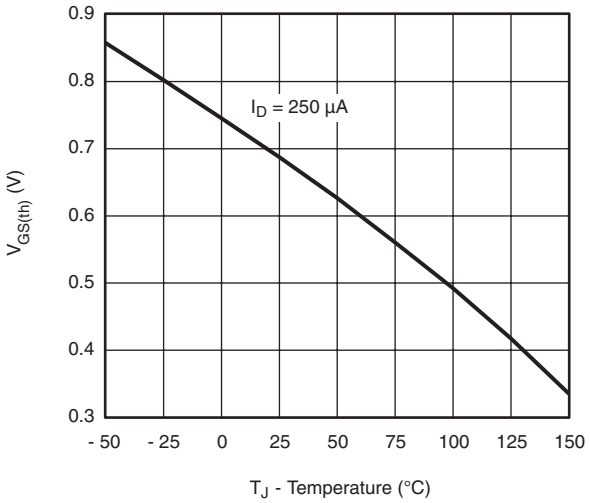
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



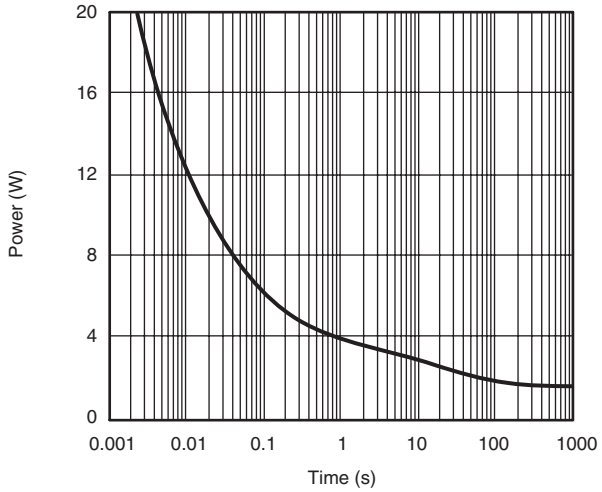
Soure-Drain Diode Forward Voltage



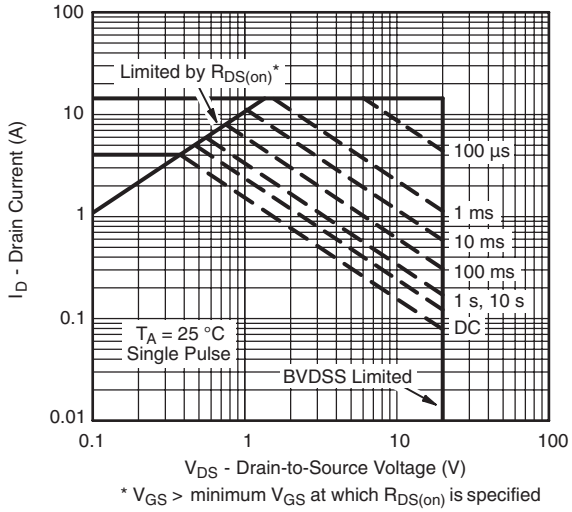
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



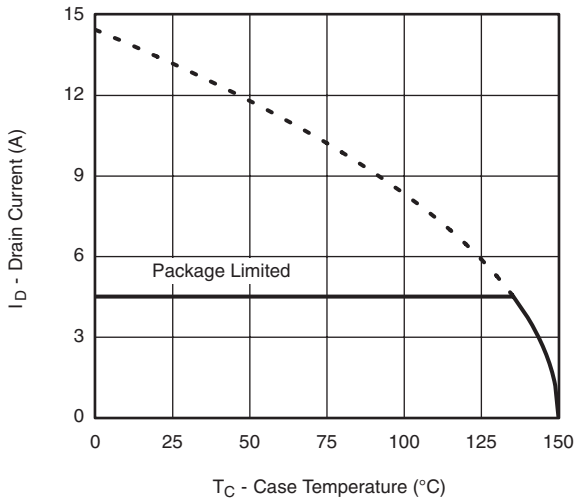
Single Pulse Power, Junction-to-Ambient



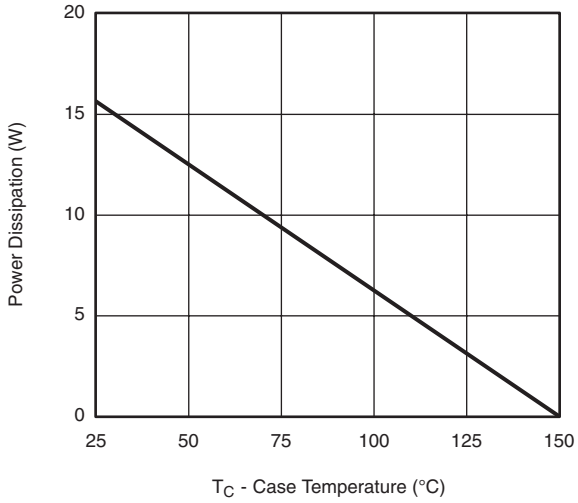
* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



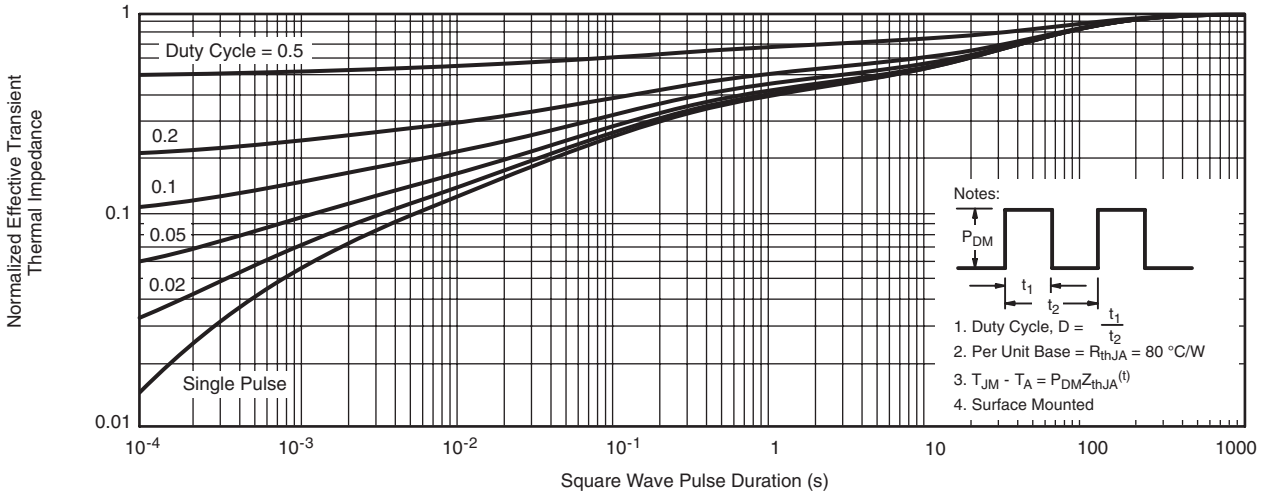
Current Derating*



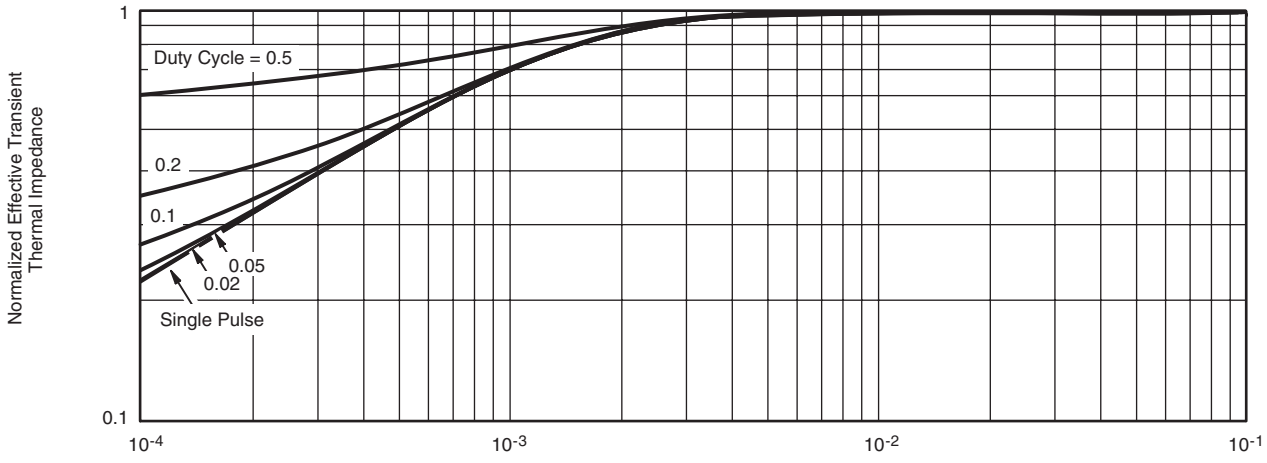
Power Derating

* The power dissipation P_D is based on $T_{J(max)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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